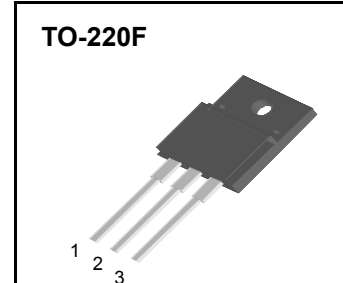
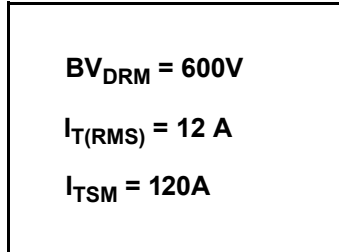
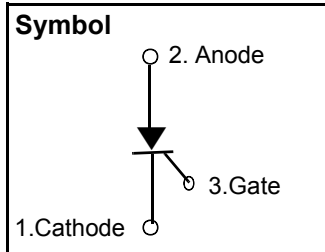


Standard Gate Silicon Controlled Rectifiers



Features

- ◆ Repetitive Peak Off-State Voltage : 600V
- ◆ R.M.S On-State Current ($I_{T(RMS)} = 12 A$)
- ◆ ISOLATED TYPE

General Description

Apollo Electron's SCR is suitable for the application where requiring high bidirectional blocking voltage capability and also suitable for over voltage protection, motor control circuit in power tool, inrush current limit circuit and heating control system.

Absolute Maximum Ratings ($T_j = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Condition	Ratings	Units
V_{DRM}	Repetitive Peak Off-State Voltage	sine wave, 50 to 60Hz	600	V
$I_{T(RMS)}$	R.M.S On-State Current	180° Conduction Angle	12	A
I_{TSM}	Surge On-State Current	1/2 Cycle, 60Hz, Sine Wave Non-Repetitive	120	A
di/dt	Critical rate of rise of on-state current	$I_{pk} = 20A, I_{GT} = 20mA$	50	A/us
$P_{G(AV)}$	Forward Average Gate Power Dissipation	$T_j = 110^\circ C$	0.5	W
T_j	Operating Junction Temperature		- 40 ~ 125	°C
T_{STG}	Storage Temperature		- 40 ~ 150	°C



Electrical Characteristics ($T_j = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Symbol	Items	Conditions	Ratings			Unit
			Min.	Typ.	Max.	
I_{DRM}	Repetitive Peak Off-State Current	$V_D = V_{DRM}$	—	—	2	mA
V_{TM}	Peak On-State Voltage (1)	$I_T = 12\text{ A}$	—	—	1.7	V
I_{GT}	Gate Trigger Current (2)	$V_D = 12\text{ V}$, $R_L = 100\ \Omega$	—	—	20	mA
V_{GT}	Gate Trigger Voltage (2)	$V_D = 12\text{ V}$, $R_L = 100\ \Omega$	---	---	1.3	V
dv/dt	Critical Rate of Rise Off-State Voltage	Linear slope upto $V_D = V_{DRM} 67\%$, Gate open $T_j = 110\text{ }^\circ\text{C}$	20	—	—	V/us
I_H	Holding Current	$V_D = 24\text{ V}$, $I_{GT} = 50\text{ mA}$	---	---	30	mA



Fig 1. Gate Characteristics

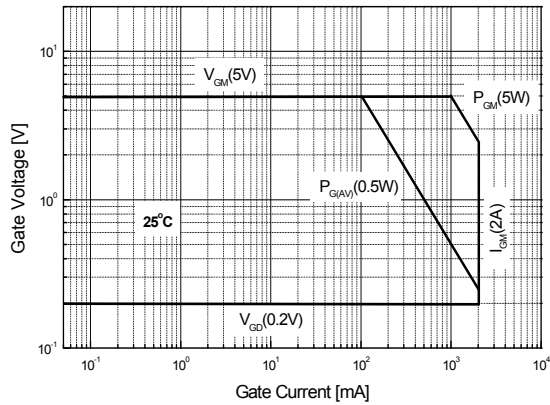


Fig 2. Maximum Case Temperature

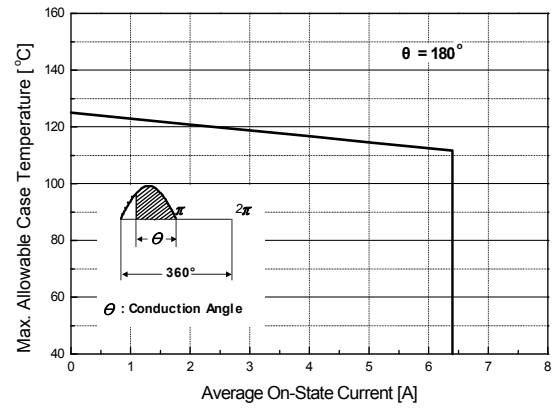


Fig 3. Typical Forward Voltage

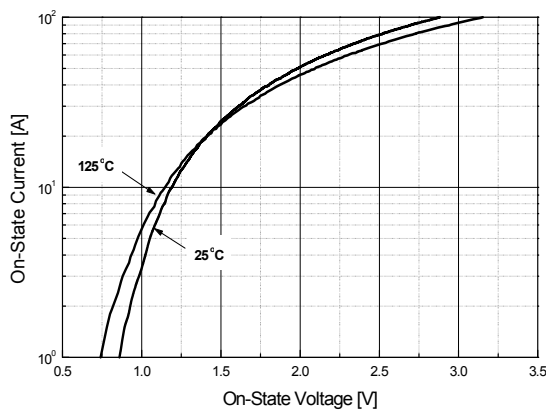


Fig 4. Thermal Response

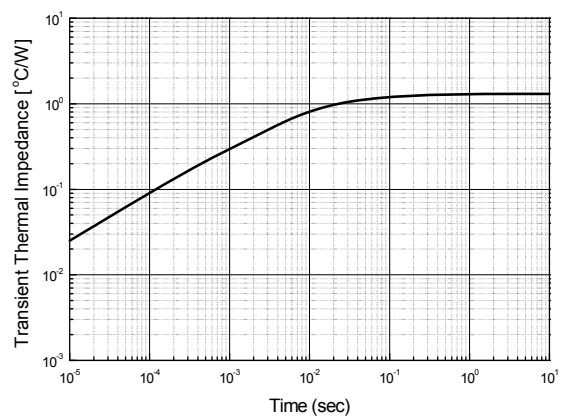


Fig 5. Typical Gate Trigger Voltage vs. Junction Temperature

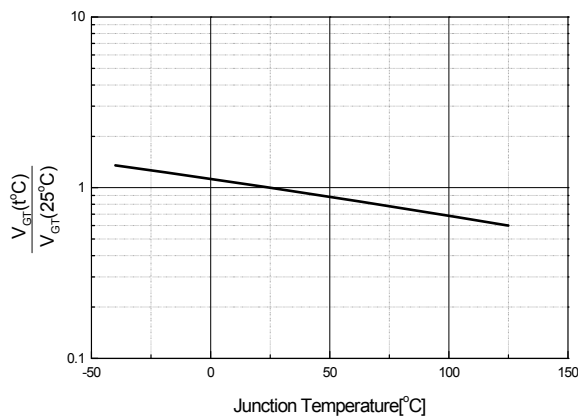
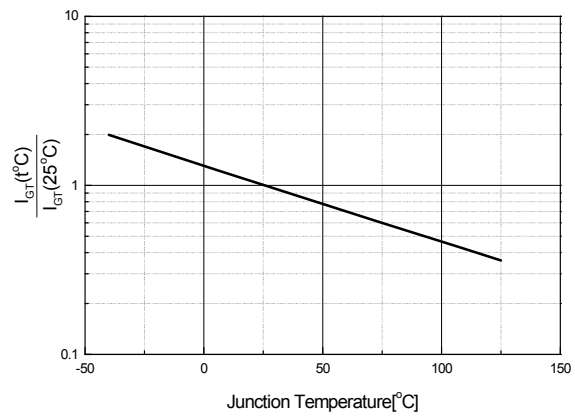


Fig 6. Typical Gate Trigger Current vs. Junction Temperature



CP10C60



Fig 7. Typical Holding Current

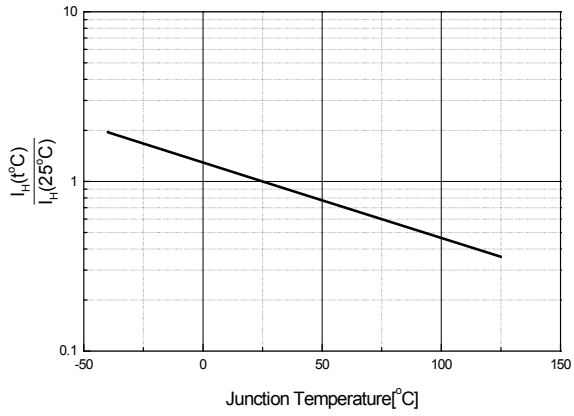
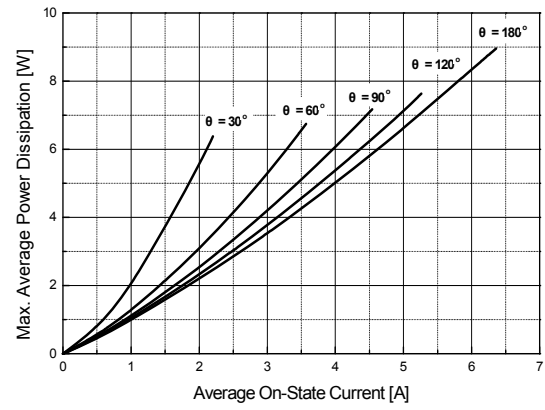
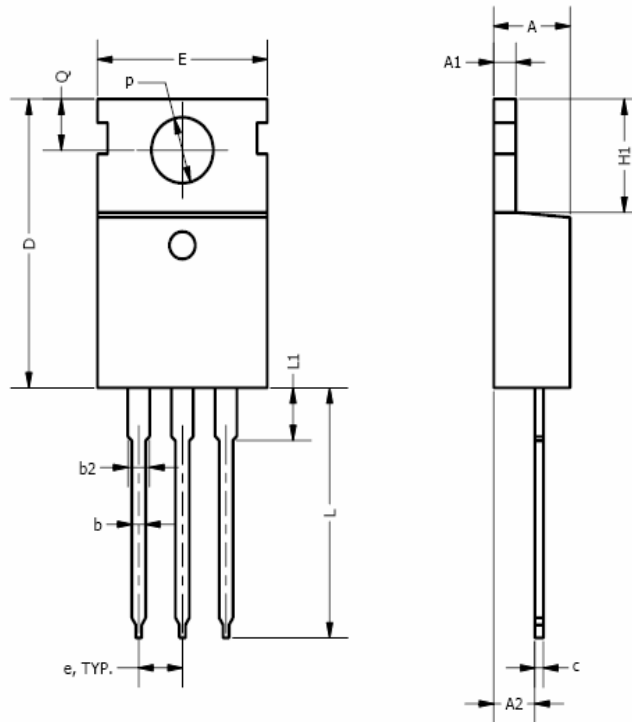


Fig 8. Power Dissipation





TO-220 Package Dimension



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.14	0.19	3.56	4.83
A1	0.02	0.055	0.51	1.4
A2	0.08	0.115	2.03	2.92
b	0.015	0.04	0.38	1.02
b2	0.045	0.07	1.14	1.78
c	0.014	0.024	0.36	0.61
D	0.56	0.65	14.22	16.51
e	0.096	0.104	2.44	2.64
E	0.38	0.42	9.65	10.67
H1	0.23	0.27	5.84	6.86
L	0.5	0.58	12.7	14.73
L1	-	0.25	-	6.35
∅ P	0.139	0.161	3.53	4.09
Q	0.1	0.135	2.54	3.43